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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number 10/022,364

Filing Date 12-20-01

First Named Inventor Kub et al

Group Art Unit 2802

Examiner Name

Attorney Docket Number NC 79,684

<i>₹ </i>				U.S. PATENT DOCU	MENTS	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Application Number 10/022364

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First Named Inventor Kub et al

Group Art Unit 2873

Examiner Name

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Sheet 2 of 3 Attorney Docket Number NC 79,684

<u> </u>	·	OTHER PRIOR ART. MON PATENT LITERATURE POOLINGING		
Examiner Initials	Cite No.1	OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Τ2	
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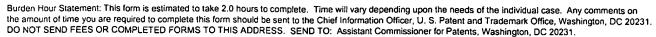
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